

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	600	WELL\$3 near8 bur\$4 near8 (implant\$6 or inplant\$6)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/11/07 09:44
2	BRS	L2	148583	(MOSFET or CMOS or BICMOS or (metal adj oxide adj semiconductor adj field adj effect adj transistor) or (complementary adj metal adj oxide adj semiconductor))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/11/07 09:45
3	BRS	L3	367	1 and 2	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/11/07 09:48
4	BRS	L4	475532 6	after\$4 or subsequent\$4	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/11/07 09:48
5	BRS	L5	311	3 and 4	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/11/07 09:57

	Typ	L #	Hits	Search Text	DBs	Time Stamp
6	IS&R	L6	180	(438/153).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/11/07 09:58
7	IS&R	L7	509	(438/199).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/11/07 09:58
8	IS&R	L8	718	(438/154).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/11/07 09:58
9	IS&R	L9	34	(438/188).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/11/07 09:58
10	IS&R	L10	135	(438/225).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/11/07 09:58

	Type	L #	Hits	Search Text	DBs	Time Stamp
11	IS&R	L11	252	(438/276).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/11/07 09:59
12	BRS	L13	948	(P near2 base) near8 (WELL\$3)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/11/07 10:12
13	BRS	L14	143	13 same (implant\$4 or inplant\$4)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/11/07 10:14
14	BRS	L16	117	14 and 2	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/11/07 10:15

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	16426	(threshold or channel\$3) near4 (implant\$6 or inplant\$6)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/11/07 16:05
2	BRS	L2	284039 5	WELL\$3	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/11/07 16:06
3	BRS	L3	12402	(STI or LOCOS or (shallow adj trench adj isolation))	USPAT	2003/11/07 16:06
4	BRS	L4	2932	((threshold or channel\$3) near4 (implant\$6 or inplant\$6)) same WELL\$3	USPAT	2003/11/07 16:06
5	BRS	L6	1693	((threshold or channel\$3) near4 (implant\$6 or inplant\$6)) and WELL\$3 and ((MOSFET or CMOS or BICMOS or (metal adj oxide adj semiconductor adj field adj effect adj transistor) or (complementary adj metal adj oxide adj semiconductor))) and ((STI or LOCOS or (shallow adj trench adj isolation)))	USPAT	2003/11/07 16:06
6	BRS	L7	864	((threshold or channel\$3) near4 (implant\$6 or inplant\$6)) same WELL\$3) and ((MOSFET or CMOS or BICMOS or (metal adj oxide adj semiconductor adj field adj effect adj transistor) or (complementary adj metal adj oxide adj semiconductor))) and ((STI or LOCOS or (shallow adj trench adj isolation)))	USPAT	2003/11/07 16:06

	Type	L #	Hits	Search Text	DBs	Time Stamp
7	BRS	L9	600	WELL\$3 near8 bur\$4 near8 (implant\$6 or inplant\$6)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/11/07 16:06
8	BRS	L10	148583	(MOSFET or CMOS or BICMOS or (metal adj oxide adj semiconductor adj field adj effect adj transistor) or (complementary adj metal adj oxide adj semiconductor))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/11/07 16:06
9	BRS	L12	475532 6	after\$4 or subsequent\$4	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/11/07 16:06
10	IS&R	L18	135	(438/225).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/11/07 16:06
11	BRS	L19	948	(P near2 base) near8 (WELL\$3)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/11/07 16:06

	Type	L #	Hits	Search Text	DBs	Time Stamp
12	BRS	L5	107	((threshold or channel\$3) near4 (implant\$6 or implant\$6)) same WELL\$3 same ((MOSFET or CMOS or BICMOS or (metal adj oxide adj semiconductor adj field adj effect adj transistor) or (complementary adj metal adj oxide adj semiconductor))) same ((STI or LOCOS or (shallow adj trench adj isolation)))	USPAT	2003/11/07 16:06
13	BRS	L8	757	(((threshold or channel\$3) near4 (implant\$6 or implant\$6)) same WELL\$3) and ((MOSFET or CMOS or BICMOS or (metal adj oxide adj semiconductor adj field adj effect adj transistor) or (complementary adj metal adj oxide adj semiconductor))) and ((STI or LOCOS or (shallow adj trench adj isolation))) not (((threshold or channel\$3) near4 (implant\$6 or implant\$6)) same WELL\$3 same ((MOSFET or CMOS or BICMOS or (metal adj oxide adj semiconductor adj field adj effect adj transistor) or (complementary adj metal adj oxide adj semiconductor))) same ((STI or LOCOS or (shallow adj trench adj isolation))))	USPAT	2003/11/07 16:07
14	BRS	L11	367	(WELL\$3 near8 bur\$4 near8 (implant\$6 or implant\$6)) and ((MOSFET or CMOS or BICMOS or (metal adj oxide adj semiconductor adj field adj effect adj transistor) or (complementary adj metal adj oxide adj semiconductor)))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/11/07 16:07

	Type	L #	Hits	Search Text	DBs	Time Stamp
15	BRS	L13	311	((WELL\$3 near8 bur\$4 near8 (implant\$6 or implant\$6)) and ((MOSFET or CMOS or BICMOS or (metal adj oxide adj semiconductor adj field adj effect adj transistor) or (complementary adj metal adj oxide adj semiconductor)))) and (after\$4 or subsequent\$4)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/11/07 16:07
16	IS&R	L20	252	(438/276).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/11/07 16:07
17	BRS	L21	143	((P near2 base) near8 (WELL\$3)) same (implant\$4 or implant\$4)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/11/07 16:07
18	BRS	L22	117	((P near2 base) near8 (WELL\$3)) same (implant\$4 or implant\$4)) and ((MOSFET or CMOS or BICMOS or (metal adj oxide adj semiconductor adj field adj effect adj transistor) or (complementary adj metal adj oxide adj semiconductor)))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/11/07 16:07
19	IS&R	L15	509	(438/199).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/11/07 17:08

	Type	L #	Hits	Search Text	DBs	Time Stamp
20	IS&R	L14	180	(438/153) .CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/11/07 17:29
21	IS&R	L17	34	(438/188) .CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/11/07 18:09
22	IS&R	L16	718	(438/154) .CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/11/07 18:17

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	16426	(threshold or channel\$3) near4 (implant\$6 or implant\$6)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/11/06 10:51
2	BRS	L2	284039 5	(after or subsequent\$4 on...) Same WELL\$3 near 8 buried near 8 (implant\$6 or and implant\$6)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/11/06 10:51
3	BRS	L3	148583	(MOSFET or CMOS or BICMOS or (metal adj oxide adj semiconductor adj field adj effect adj transistor) or (complementary adj metal adj oxide adj semiconductor))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/11/06 10:53
4	BRS	L4	12402	(STI or LOCOS or (shallow adj trench adj isolation))	USPAT	2003/11/06 10:54
5	BRS	L5	2932	1 same 2	USPAT	2003/11/06 10:55
6	BRS	L6	107	1 same 2 same 3 same 4	USPAT	2003/11/06 11:05
7	BRS	L8	1693	1 and 2 and 3 and 4	USPAT	2003/11/06 11:06
8	BRS	L9	864	(1 same 2) and 3 and 4	USPAT	2003/11/06 11:06
9	BRS	L10	757	9 not 6	USPAT	2003/11/06 11:06